IN THE SPECIFICATION:

Please amend the specification as follows:

Paragraph beginning on page 11, at prenumbered line 2, has been amended as follows:

Now the description will be made to a second method embodiment according to the present application, and please refer directly to Fig. 4. The second method embodiment is the same as the preferred embodiment except for the step, Step 6'. Step 6': coating a transparent contact layer (TCL) with a suitable thickness over the contact layer, p-GaN based layer, succeeding to Step 5. In terms of material used, the TCL may be made of Ni/Au and other suitable transparent (for the generated light from the light-emitting structure, such as a light with a wavelength of 380-600nm) and conductive materials and may be an n-TCL (n-doped) or a p-TCL (p-doped). In fact, the TCL may be a doped metal oxide, such as doped ZnO, which may be referenced to U.S. patent application ~~(please refer to the two our co-filling cases, after they obtain application numbers),~~ application no. 10/700,536, filed on November 5, 2003, now U.S. patent no. 6,992,331; and U.S. patent application no. 10/700,537, filed November 5, 2005, currently pending, and co-pending with the present application and assigned to the same assignee of the present invention.